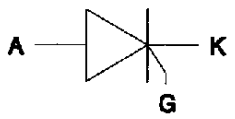
SGS-THOMSON MICROELECTRONICS

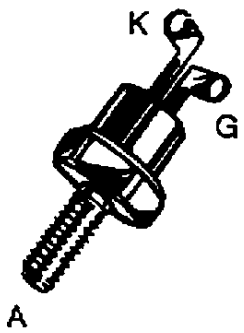
2N 1771 ---> 2N 2619

SCR

FEATURES

- HIGH SURGE CAPABILITY
- HIGH ON-STATE CURRENT
- HIGH STABILITY AND RELIABILITY





TO 64
(Metal)

DESCRIPTION

The 2N 1771 ---> 2N 2619 Family of Silicon Controlled Rectifiers uses a high performance glass passivatedt technology.
This general purpose Family of Silicon Controlled Rectifiers is designed for power supplies up to 400Hz on resistive or inductive load.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)	Tc = 105 °C	7.4	A
$I_{T(AV)}$	Average on-state current (180° conduction angle, single phase circuit)	Tc = 105 °C	4.7	A
I_{TSM}	Non repetitive surge peak on-state current (Tj initial = 25°C)	tp = 8.3 ms	84	A
		tp = 10 ms	80	
I^2t	I^2t value	tp = 10 ms	32	A^2s
dI/dt	Critical rate of rise of on-state current Gate supply : I_G = 150 mA di_G/dt = 1 A/µs		100	A/µs
Tstg Tj	Storage and operating junction temperature range		- 40 to + 150 - 40 to + 125	°C °C
Tl	Maximum lead temperature for soldering during 10 s at 4.5 mm from case		230	°C

Symbol	Parameter	2N					Unit
		1771	1772	1774	1777	2619	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Tj = 125 °C	50	100	200	400	600	V

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth (c-h)	Contact (case to heatsink)	0.4	°C/W
Rth (j-c) DC	Junction to case for DC	2.5	°C/W

GATE CHARACTERISTICS (maximum values)

$P_{G\ (AV)}$ = 1W P_{GM} = 20W (tp = 20 µs) I_{FGM} = 4A (tp = 20 µs) V_{FGM} = 16V (tp = 20 µs) V_{RGM} = 5 V.

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Value	Unit
I_{GT}	V_D=12V (DC) R_L=33Ω	Tj=25°C	MAX	15	mA
V_{GT}	V_D=12V (DC) R_L=33Ω	Tj=25°C	MAX	1.5	V
V_{GD}	V_D=V_{DRM} R_L=3.3kΩ	Tj= 125°C	MIN	0.2	V
tgt	V_D=V_{DRM} I_G = 200mA dI_G/dt = 1.5A/µs	Tj=25°C	TYP	2	µs
I_L	I_G= 1.2 I_{GT}	Tj=25°C	TYP	40	mA
I_H	I_T= 100mA gate open	Tj=25°C	MAX	30	mA
V_{TM}	ITM= 15A tp= 380µs	Tj=25°C	MAX	1.85	V
I_{DRM} I_{RRM}	V_{DRM} Rated V_{RRM} Rated	Tj=25°C	MAX	0.02	mA
		Tj= 125°C		2	
dV/dt	Linear slope up to V_D=67%V_{DRM} gate open	Tj= 125°C	MIN	200	V/µs
Tq	V_D=67%V_{DRM} I_{TM}= 15A V_R= 24V dI_{TM}/dt=30 A/µs dV_D/dt= 20V/µs	Tj= 125°C	TYP	70	µs

Fig.1 : Maximum average power dissipation versus average on-state current.

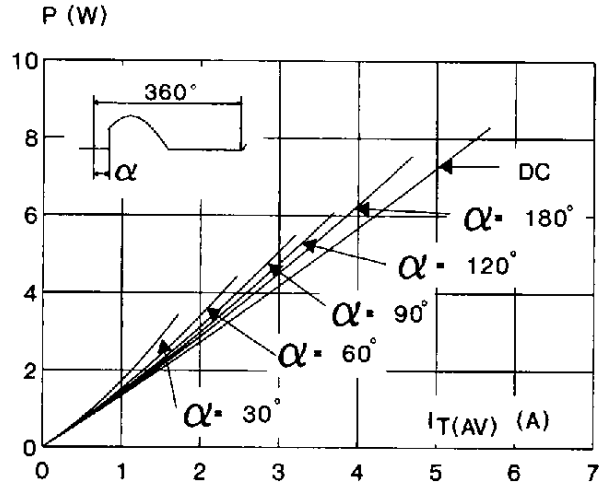


Fig.2 : Correlation between maximum average power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact.

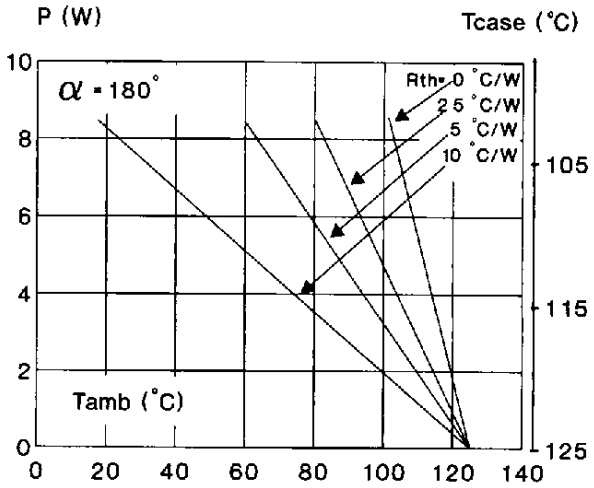


Fig.3 : Average on-state current versus case temperature.

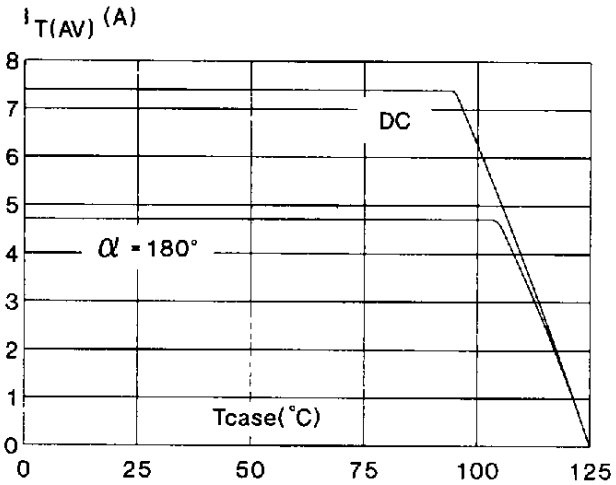


Fig.4 : Thermal transient impedance junction to ambient versus pulse duration.

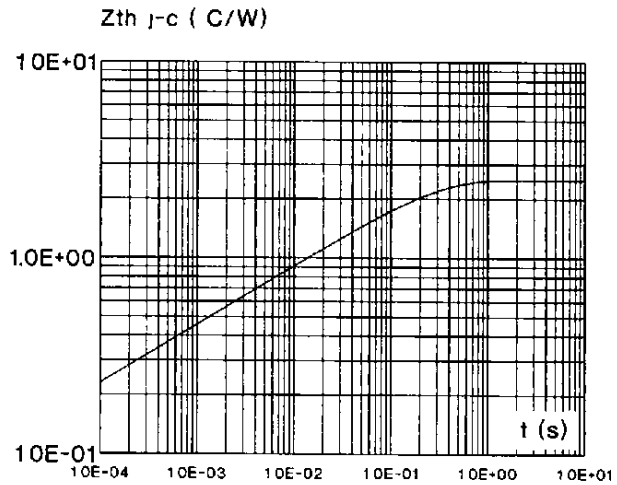


Fig.5 : Relative variation of gate trigger current versus junction temperature.

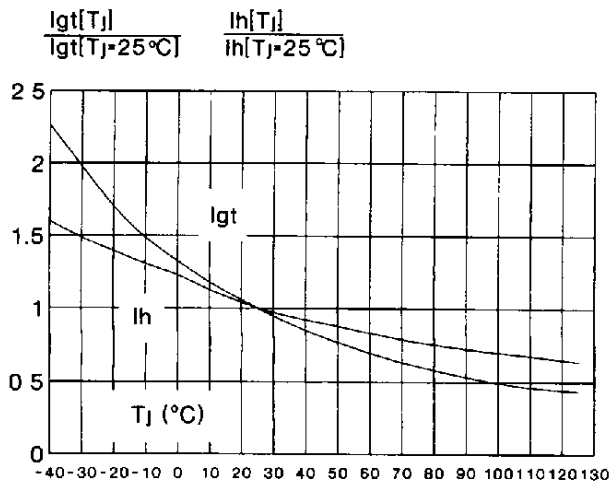


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.

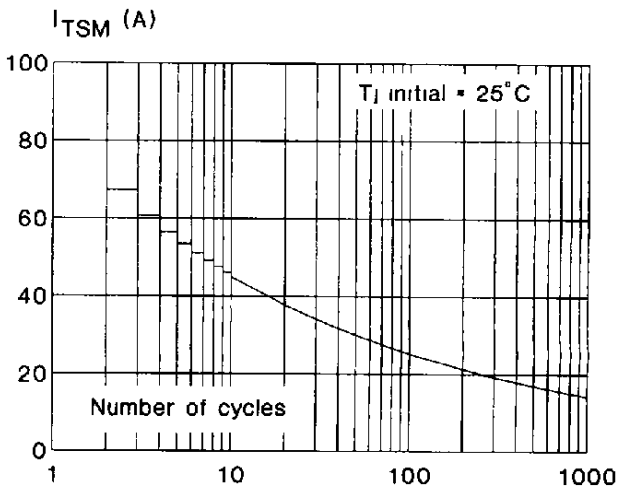


Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : t ≤ 10 ms, and corresponding value of I^2t.

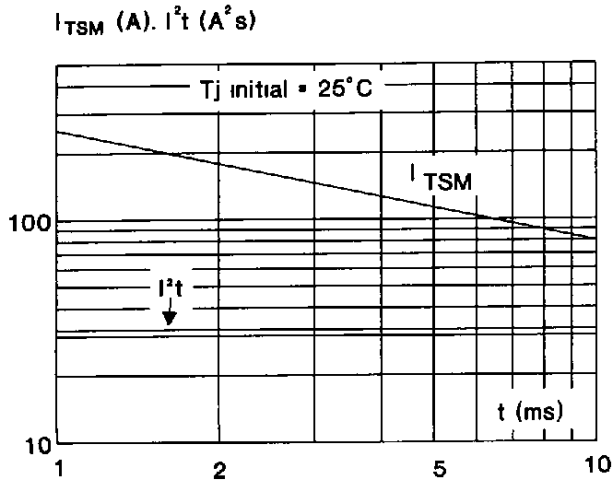
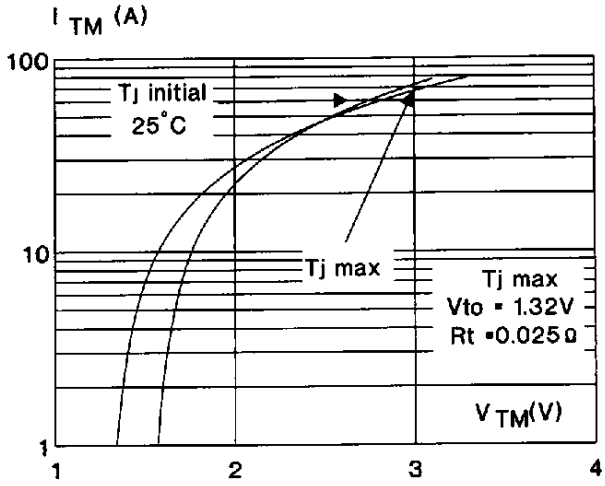
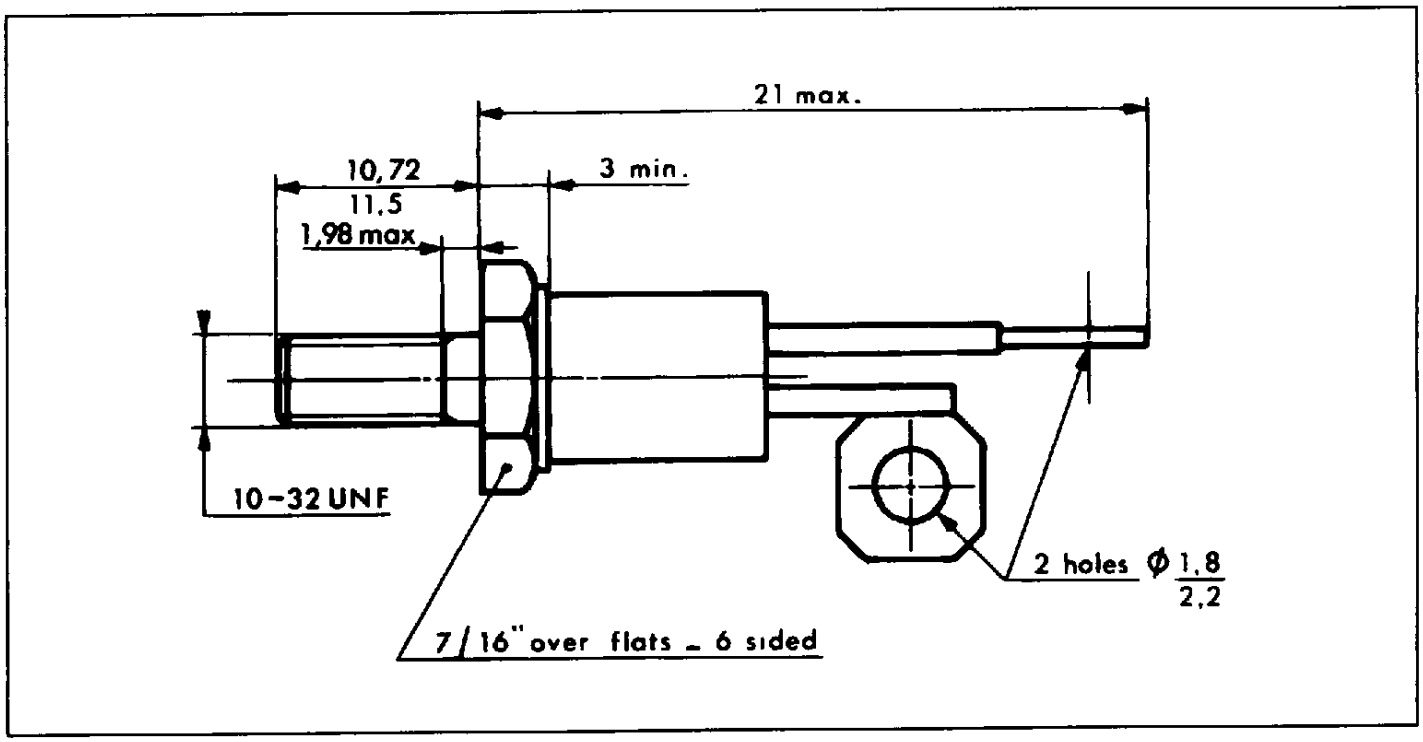


Fig.8 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA (in millimeters)

TO 64 Metal



Cooling method : A
Marking : type number
Weight : 5 g
Polarity : Anode (or A2) to case
Stud torque : 3.5 mΛN min / 3.8 mΛN max